

OPA6625

Ultra Bright

Red LED Chip

GaAlAs / GaAs

1. Material Substrate GaAs (P Type) Removed
Epitaxial Layer GaAlAs (N/P Type)

2. Electrode N (Cathode) Side Gold Alloy
P (Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.6		V	$I_F=1\text{mA}$
	$V_{F(2)}$		1.8	2.3	V	$I_F=20\text{mA}$
Reverse Voltage	V_R	4.0			V	$I_R=10\mu\text{A}$
Brightness	I_V	1300	1800		mcd	$I_F=20\text{mA}$
Wavelength	Hue		645		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		22		nm	$I_F=20\text{mA}$

※ Note: Assembled into T1^{3/4} plastic package.

4. Mechanical Data

- (a) Emission Area ----- 12mil × 12mil
- (b) Bottom Area ----- 14mil × 14mil
- (c) Chip Thickness ----- 8mil

